**Product data sheet** 

# 1. General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

### 2. Features and benefits

- Isolated plastic package
- Low leakage current
- Low thermal resistance
- Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT

# 3. Applications

- Active PFC in air conditioner
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage			6	00		V
$I_{F(AV)}$	average forward current	$δ = 0.5$ ; square-wave pulse; $T_h \le 51$ °C; Fig. 1; Fig. 2; Fig. 3	30			А	
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 μs; $T_h \le$ 51 °C; square-wave pulse	60			А	
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4				А	
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse				Α	
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2	2.75	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.38	1.8	V
Dynamic	characteristics						
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 50 \text{ A}/\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7		-	-	35	ns

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	А	anode		K <b>- </b> A
mb	n.c.	mounting base; isolated		001aaa020
			SOD113 (2-lead TO-220F)	

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package				
	Name	Description	Version		
BYC30X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113		

# 7. Marking

#### **Table 4. Marking codes**

Type number	Marking codes
BYC30X-600P	BYC30X-600P

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		600	V
$V_{\text{RWM}}$	crest working reverse voltage		600	V
$V_R$	reverse voltage	DC	600	V
I <sub>F(AV)</sub>	average forward current	$δ = 0.5$ ; square-wave pulse; $T_h \le 51$ °C; Fig. 1; Fig. 2; Fig. 3	30	А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>h</sub> ≤ 51 °C; square-wave pulse	60	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	200	Α
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	220	Α
T <sub>stg</sub>	storage temperature		-65 to 175	°C
T <sub>j</sub>	junction temperature		175	°C

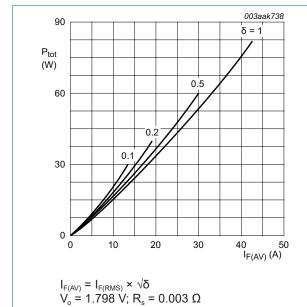
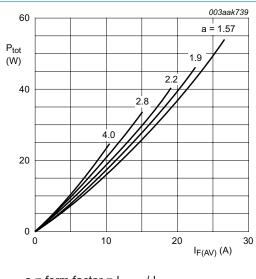


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$  $V_o$  = 1.798 V;  $R_s$  = 0.003  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

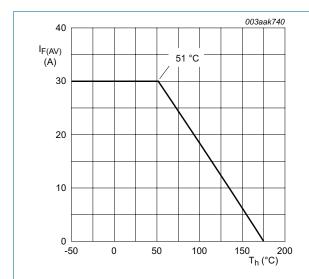


Fig. 3. Forward current as a function of heatsink temperature; maximum values

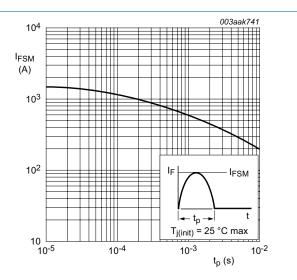
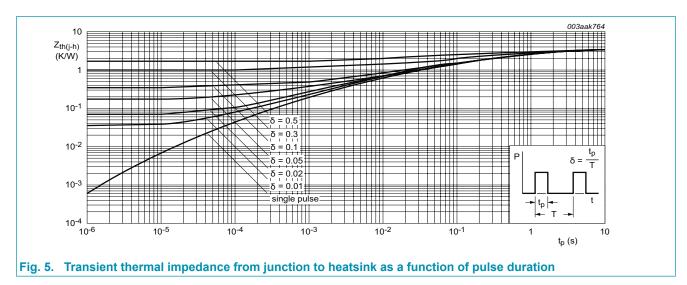


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; Fig 5	-	-	3.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



### 10. Isolation characteristics

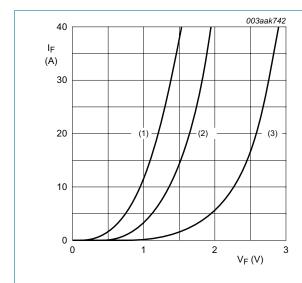
#### **Table 7. Isolation characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	PF

### 11. Characteristics

**Table 8. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	2	2.75	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	1.38	1.8	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C	-	-	600	μA
Dynamic	characteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	35	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	35	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	70	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	3.5	-	А
		$I_F = 30 \text{ A}$ ; $V_R = 200 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 125 \text{ °C}$ ; Fig. 7	-	7.6	-	А
Q <sub>r</sub>	recovered charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	50	-	nC
		$I_F = 30 \text{ A; } V_R = 200 \text{ V; } dI_F/dt = 200 \text{ A/}\mu\text{s;}$ $T_i = 125 \text{ °C; } Fig. 7$	-	280	-	nC



 $V_o = 1.798 \text{ V}; R_s = 0.003 \Omega$ 

(1)  $T_j = 150 \, ^{\circ}C$ ; typical values

(2)  $T_i = 150 \,^{\circ}\text{C}$ ; maximum values

(3)  $T_i = 25$  °C; maximum values

Fig. 6. Forward current as a function of forward voltage

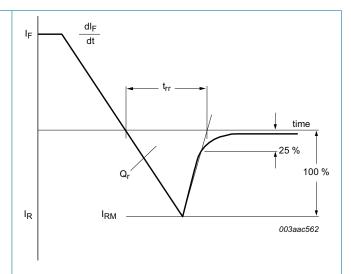
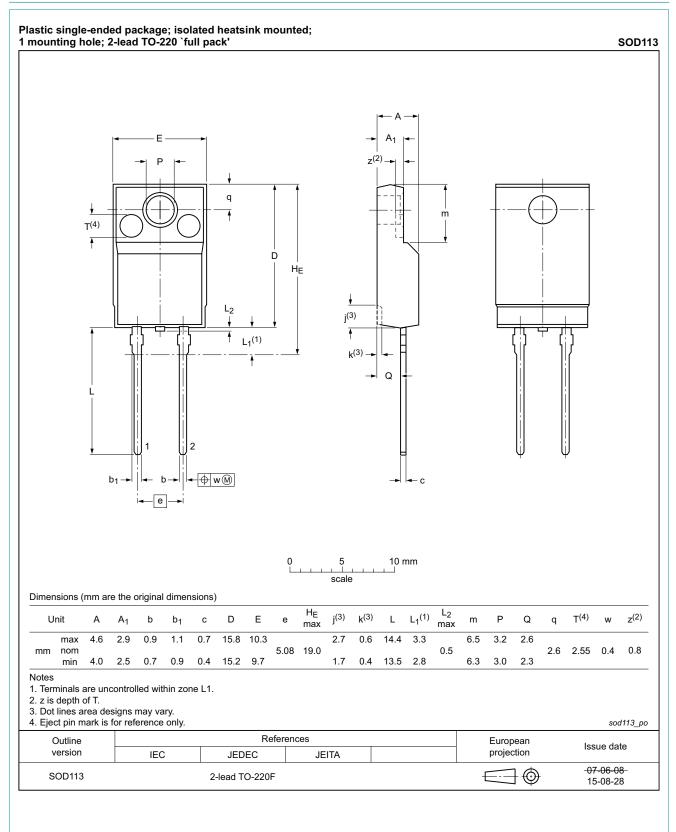


Fig. 7. Reverse recovery definitions; ramp recovery

# 12. Package outline



### 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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**BYC30X-600P** 

**Ultrafast power diode** 

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